

ANTREX Electronics

Electronic Components Sourcing Information

Product Reference Information

Part Number:	NTNS3A91PZT5G
Manufacturer:	onsemi
Package:	Please confirm with sales
Availability:	Please confirm with sales

Product Page:

<https://antrexco.com/product/details/onsemi/ntns3a91pzt5g.html>

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Contact Information

Email: info@antrexco.com

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Quality & Trust

New & Original Components

Supplier verification and packaging condition review

CoC / RoHS / REACH documents available on request

Secure sourcing support for OEM / EMS projects

Note:

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

NTNS3A91PZ

MOSFET – Single, P-Channel, Small Signal, XLLGA3, 0.62 x 0.62 x 0.4 mm -20 V, -223 mA

Features

- Single P-Channel MOSFET
- Ultra Small and Thin Package (0.62 x 0.62 x 0.4 mm)
- Low $R_{DS(on)}$ Solution in 0.62 x 0.62 mm Package
- 1.5 V Gate Voltage Rating
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Small Signal Load Switch
- Analog Switch
- High Speed Interfacing
- Optimized for Power Management in Ultra Portable Products

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter			Symbol	Value	Units
Drain-to-Source Voltage			V_{DSS}	-20	V
Gate-to-Source Voltage			V_{GS}	± 8.0	V
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	I_D	-223	mA
		$T_A = 85^\circ\text{C}$		-161	
	$t \leq 5 \text{ s}$	$T_A = 25^\circ\text{C}$		-240	
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	P_D	121	mW
	$t \leq 5 \text{ s}$	$T_A = 25^\circ\text{C}$		140	
Pulsed Drain Current		$t_p = 10 \mu\text{s}$	I_{DM}	-669	mA
Operating Junction and Storage Temperature			T_J, T_{STG}	-55 to 150	$^\circ\text{C}$
Source Current (Body Diode)			I_S	-121	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Units
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	1035	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – $t \leq 5 \text{ s}$ (Note 1)	$R_{\theta JA}$	895	

1. Surface Mounted on FR4 Board using the minimum recommended pad size, (or 2 mm²), 1 oz Cu.



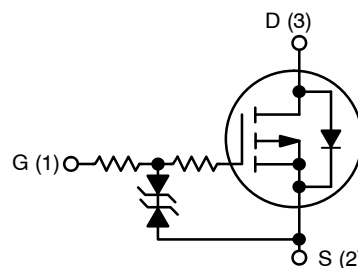
ON Semiconductor®

<http://onsemi.com>

MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
-20 V	1.6 Ω @ -4.5 V	-223 mA
	2.4 Ω @ -2.5 V	
	3.3 Ω @ -1.8 V	
	4.5 Ω @ -1.5 V	

P-Channel MOSFET



MARKING DIAGRAM



XLLGA3
CASE 713AB



D = Specific Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
NTNS3A91PZT5G	XLLGA3 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTNS3A91PZ

2. Pulse Test: pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = -250 \mu\text{A}$, ref to 25°C		11		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0 \text{ V}, V_{DS} = -20 \text{ V}$			-1.0	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8.0 \text{ V}$			± 2.0	μA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250 \mu\text{A}$	-0.4		-1.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			2.1		mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = -4.5 \text{ V}, I_D = -100 \text{ mA}$		1.1	1.6	Ω
		$V_{GS} = -2.5 \text{ V}, I_D = -50 \text{ mA}$		1.5	2.4	
		$V_{GS} = -1.8 \text{ V}, I_D = -20 \text{ mA}$		2.0	3.3	
		$V_{GS} = -1.5 \text{ V}, I_D = -10 \text{ mA}$		2.5	4.5	
Forward Transconductance	g_{FS}	$V_{DS} = -5 \text{ V}, I_D = -100 \text{ mA}$		0.41		S
Source-Drain Diode Voltage	V_{SD}	$V_{GS} = 0 \text{ V}, I_S = -10 \text{ mA}$		-0.6	-1.0	V

CHARGES & CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0 \text{ V}, f = 10 \text{ kHz}, V_{DS} = -15 \text{ V}$		41		pF
Output Capacitance	C_{OSS}			4.6		
Reverse Transfer Capacitance	C_{RSS}			4.1		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -4.5 \text{ V}, V_{DS} = -15 \text{ V}, I_D = -200 \text{ mA}$		1.1		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.1		
Gate-to-Source Charge	Q_{GS}			0.2		
Gate-to-Drain Charge	Q_{GD}			0.23		

SWITCHING CHARACTERISTICS, $V_{GS} = 4.5 \text{ V}$ (Note 3)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -4.5 \text{ V}, V_{DD} = -15 \text{ V}, I_D = -200 \text{ mA}, R_G = 2 \Omega$		41		ns
Rise Time	t_r			97		
Turn-Off Delay Time	$t_{d(OFF)}$			571		
Fall Time	t_f			286		

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

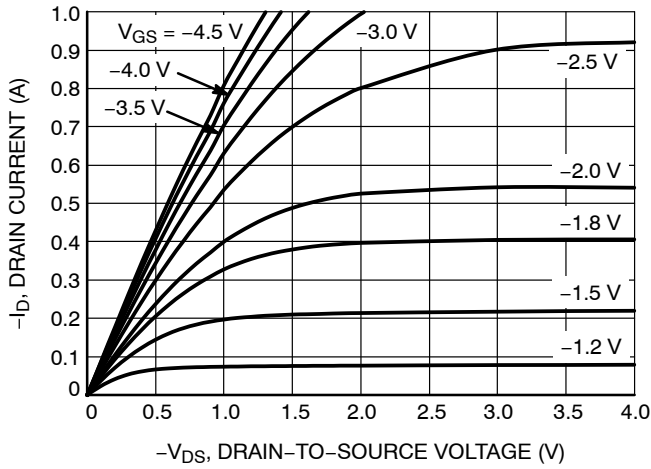


Figure 1. On-Region Characteristics

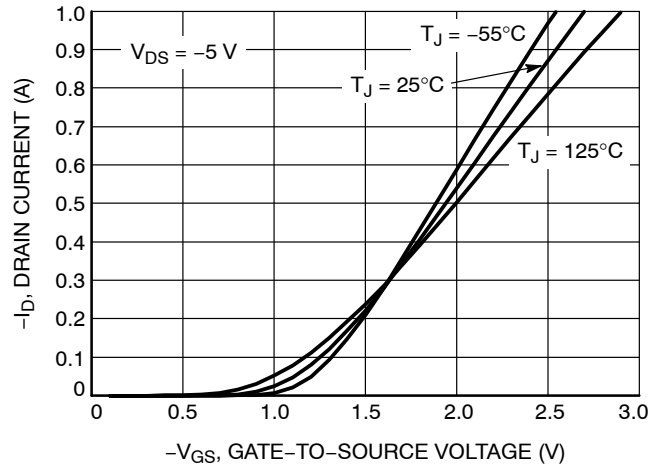


Figure 2. Transfer Characteristics

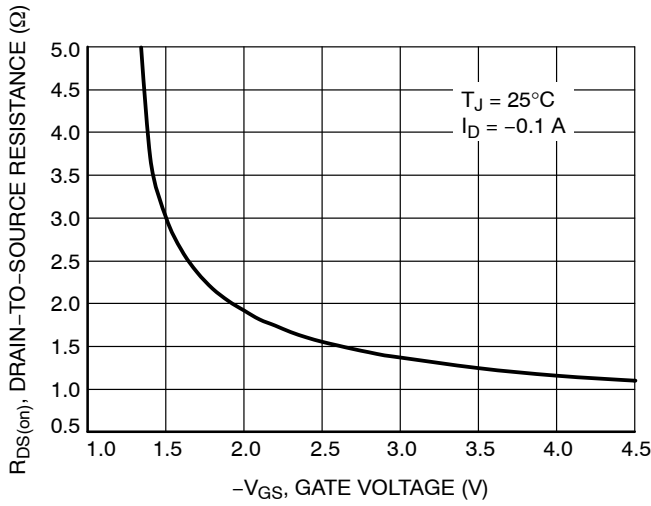


Figure 3. On-Resistance vs. Gate-to-Source Voltage

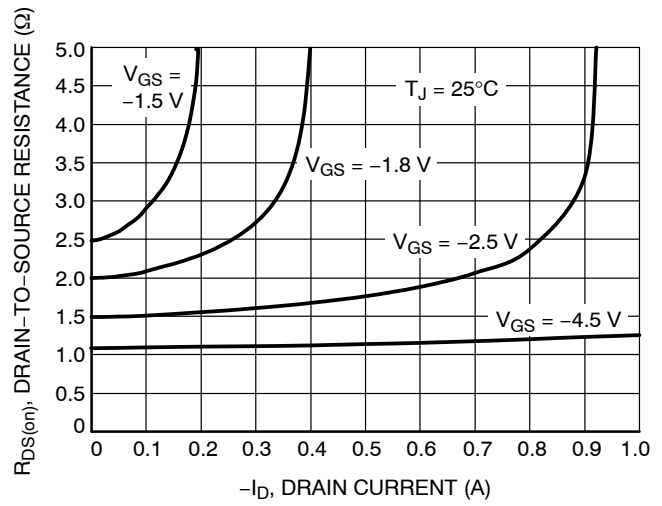


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

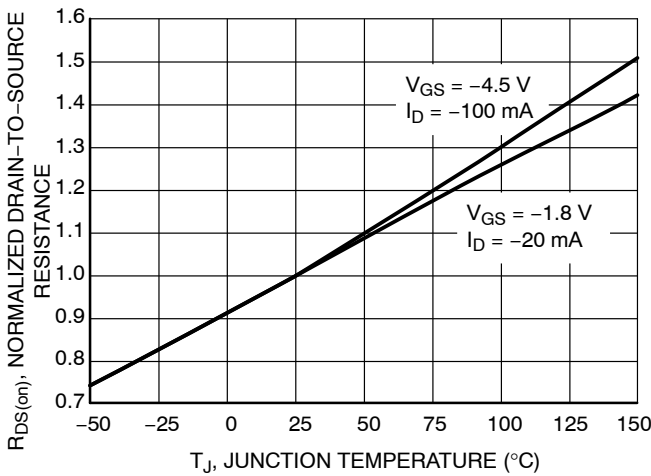


Figure 5. On Resistance Variation with Temperature

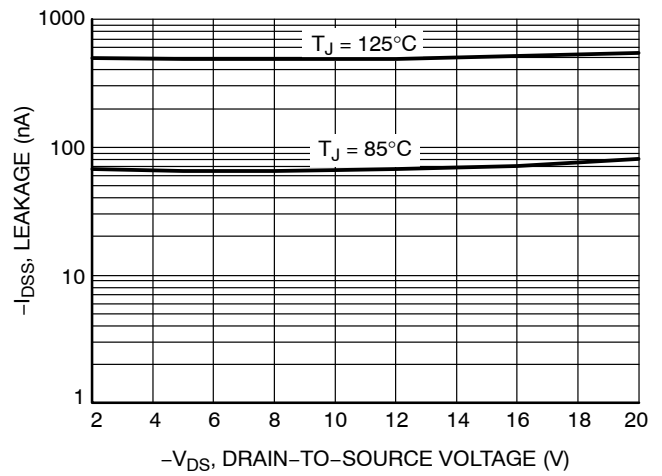


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

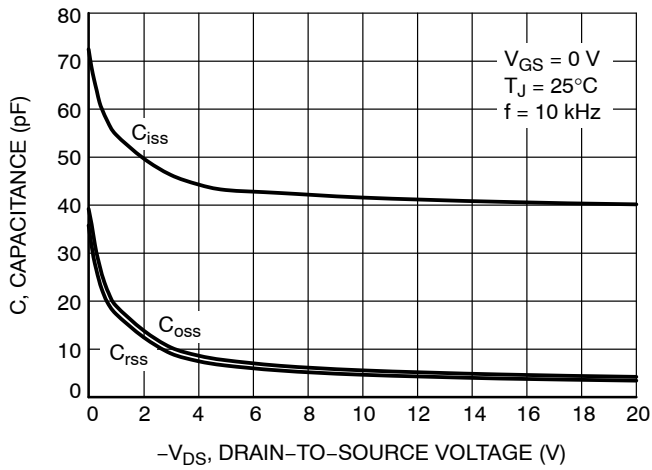


Figure 7. Capacitance Variation

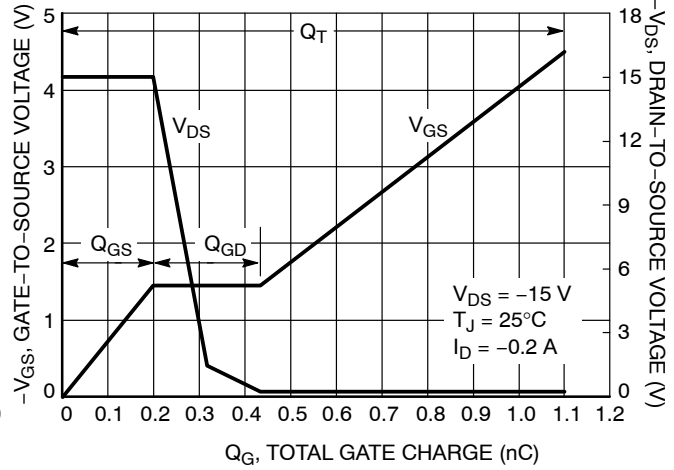


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

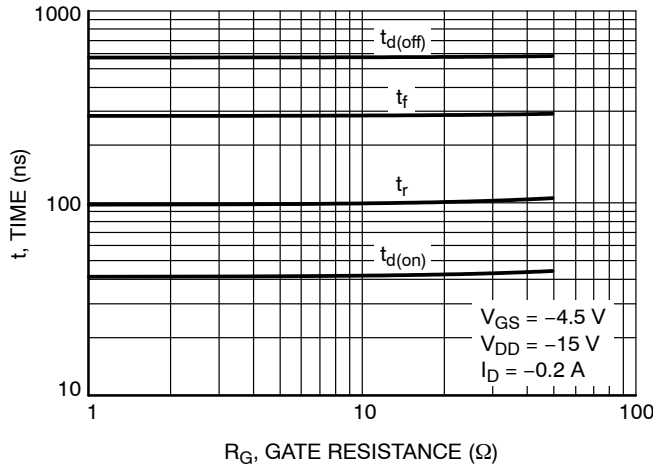


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

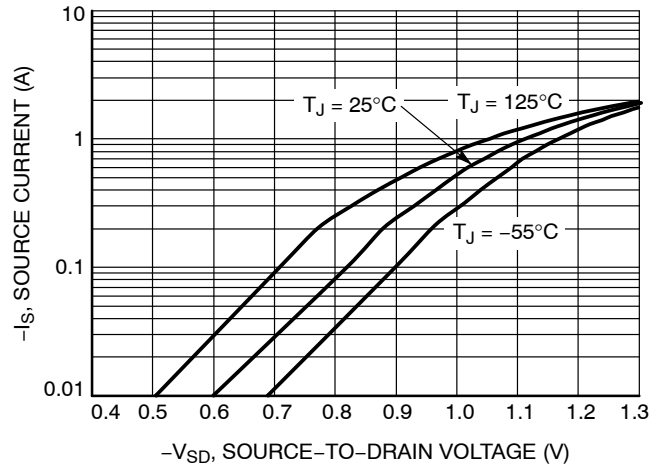


Figure 10. Diode Forward Voltage vs. Current

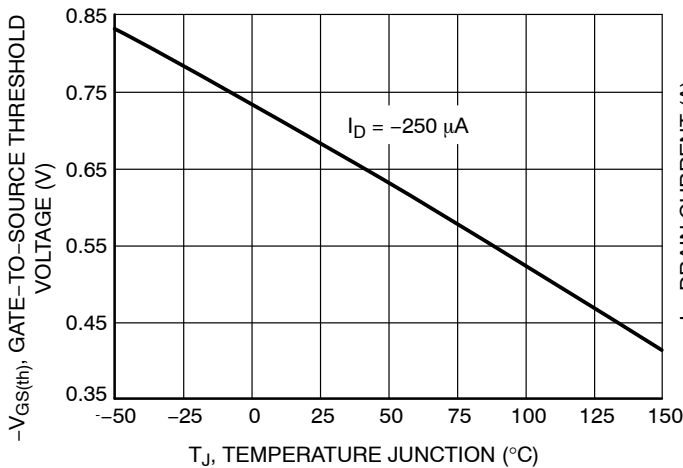


Figure 11. Threshold Voltage

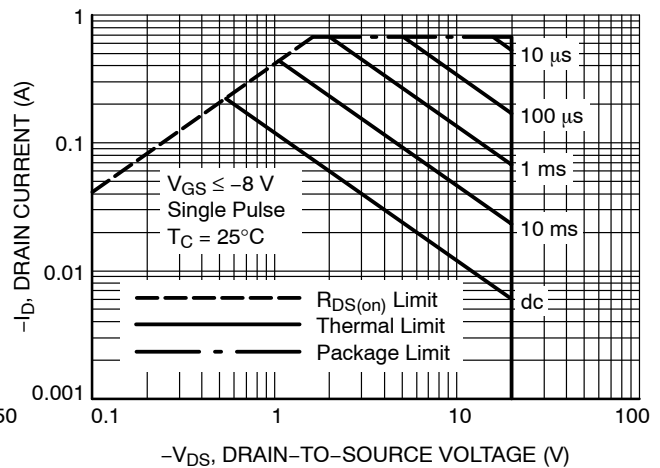


Figure 12. Maximum Rated Forward Biased Safe Operating Area

NTNS3A91PZ

TYPICAL CHARACTERISTICS

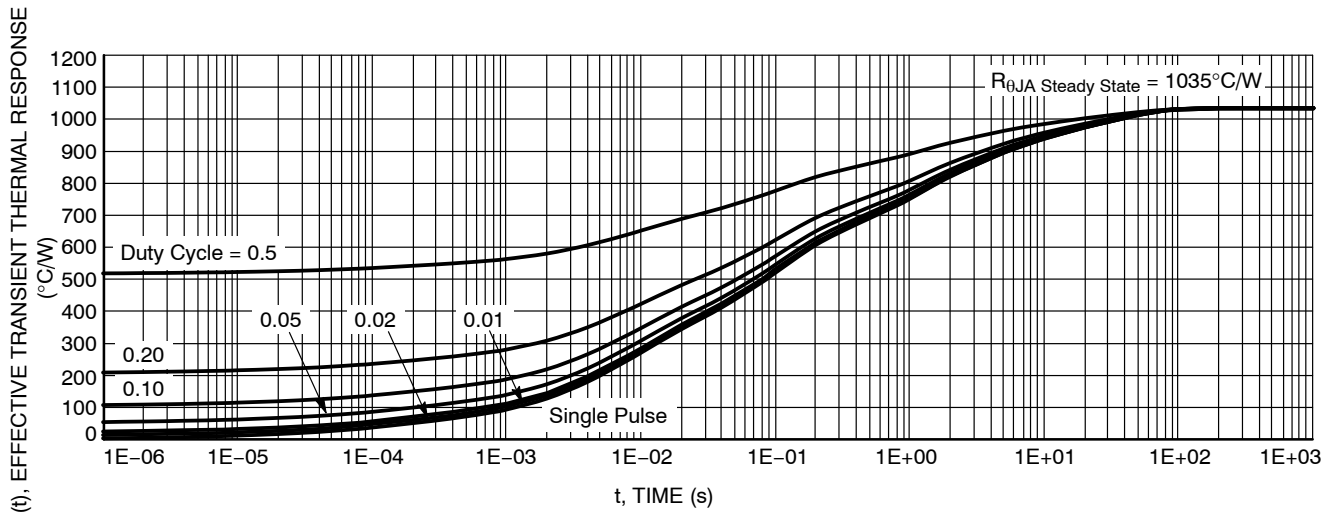
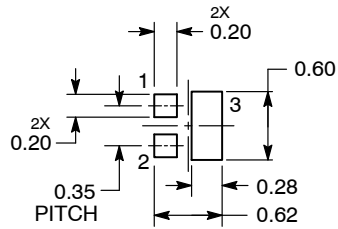


Figure 13. FET Thermal Response

MINIMUM RECOMMENDED SOLDER FOOTPRINT*



DIMENSIONS: MILLIMETERS

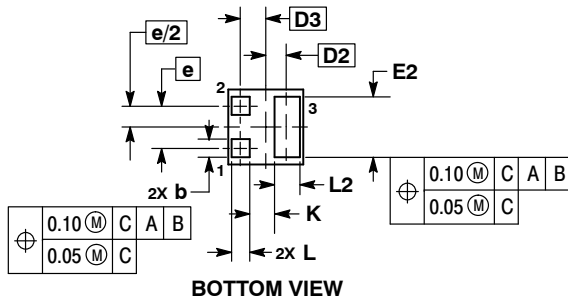
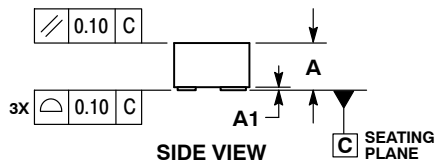
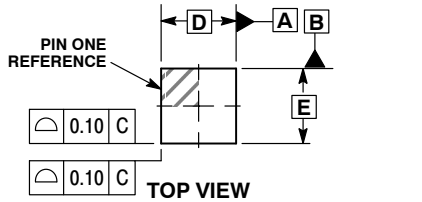
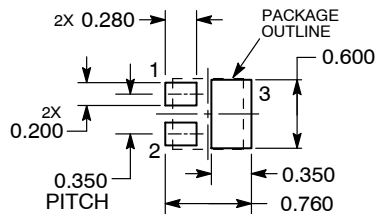
*Dependent upon end user capabilities, this footprint could be used as a minimum.



SCALE 8:1

XLLGA3, 0.62x0.62, 0.35P
CASE 713AB
ISSUE O

DATE 25 SEP 2012


**RECOMMENDED
SOLDER FOOTPRINT***


DIMENSIONS: MILLIMETERS

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.

MILLIMETERS		
DIM	MIN	MAX
A	0.340	0.440
A1	0.000	0.030
b	0.100	0.200
D	0.620	BSC
D2	0.175	BSC
D3	0.205	BSC
E	0.620	BSC
E2	0.400	0.600
e	0.350	BSC
K	0.200	REF
L	0.090	0.210
L2	0.110	0.310

**GENERIC
MARKING DIAGRAM***

X = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, [SOLDDRRM/D](#).

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DESCRIPTION:	XLLGA3, 0.62X0.62, 0.35P	PAGE 1 OF 1

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